## **APPLICATION DATA SHEET**

## Electronic Version v14

## Stylesheet Version v14.0

Title of Invention

METHOD FOR FABRICATING A VERTICAL BIPOLAR JUNCTION TRANSISTOR

Application Type : regular, utility
Attorney Docket Number : NAUP0535USA

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as our attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.